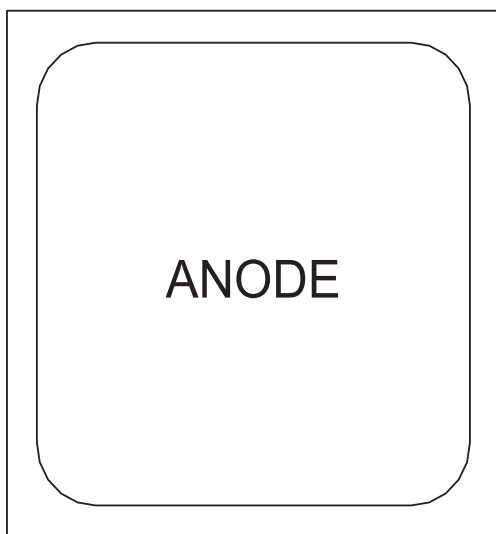


PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	50 x 50 MILS
Die Thickness	12.2 MILS
Anode Bonding Pad Area	34 x 34 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

145 Adams Avenue
Hauppauge, NY 11788 USA
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GROSS DIE PER 4 INCH WAFER

4,520

PRINCIPAL DEVICE TYPES

UES1001 thru UES1003
UF4001 thru UF4007
CMR1U-01 Series
CMR1U-01M Series

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

www.centrasemi.com/chip

R1 (1-August 2002)